

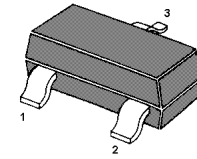
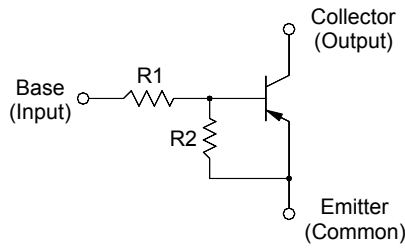
MMBTRA101SS...MMBTRA106SS

PNP Silicon Epitaxial Planar Transistor

for switching and interface circuit and drive circuit applications

Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process



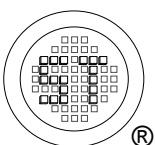
1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Resistor Values

Type	R1 (K Ω)	R2 (K Ω)
MMBTRA101SS	4.7	4.7
MMBTRA102SS	10	10
MMBTRA103SS	22	22
MMBTRA104SS	47	47
MMBTRA105SS	2.2	47
MMBTRA106SS	4.7	47

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Output Voltage		$-V_o$	50	V
Input Voltage	MMBTRA101SS	$-V_i$	20, -10	V
	MMBTRA102SS		30, -10	
	MMBTRA103SS		40, -10	
	MMBTRA104SS		40, -10	
	MMBTRA105SS		12, -5	
	MMBTRA106SS		20, -5	
Output Current		$-I_o$	100	mA
Total Power Dissipation		P_{tot}	200	mW
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	- 55 to + 150	$^\circ\text{C}$



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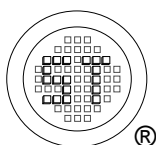


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Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_o = 5\text{ V}$, $-I_o = 10\text{ mA}$					
MMBTRA101SS	G _I	30	-	-	-
MMBTRA102SS		50	-	-	-
MMBTRA103SS		70	-	-	-
MMBTRA104SS		80	-	-	-
MMBTRA105SS		80	-	-	-
MMBTRA106SS		80	-	-	-
Output Cutoff Current at $-V_o = 50\text{ V}$	$-I_{O(OFF)}$	-	-	500	nA
Input Current at $-V_i = 5\text{ V}$					
MMBTRA101SS	-I _I	-	-	1.8	mA
MMBTRA102SS		-	-	0.88	
MMBTRA103SS		-	-	0.36	
MMBTRA104SS		-	-	0.18	
MMBTRA105SS		-	-	3.6	
MMBTRA106SS		-	-	1.8	
Output Voltage at $-I_o = 10\text{ mA}$, $-I_i = 0.5\text{ mA}$	$-V_{O(ON)}$	-	-	0.3	V
Input Voltage (ON) at $-V_o = 0.2\text{ V}$, $-I_o = 5\text{ mA}$					
MMBTRA101SS	$-V_{I(ON)}$	-	-	2	V
MMBTRA102SS		-	-	2.4	
MMBTRA103SS		-	-	3	
MMBTRA104SS		-	-	5	
MMBTRA105SS		-	-	1.1	
MMBTRA106SS		-	-	1.3	
Input Voltage (OFF) at $-V_o = 5\text{ V}$, $-I_o = 0.1\text{ mA}$					
MMBTRA101SS~104SS	$-V_{I(OFF)}$	1	-	-	V
MMBTRA105SS~106SS		0.5	-	-	
Transition Frequency at $-V_o = 10\text{ V}$, $-I_o = 5\text{ mA}$	f _T ¹⁾	-	200	-	MHz

¹⁾ Characteristic of transistor only.

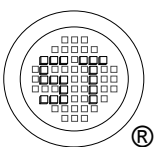
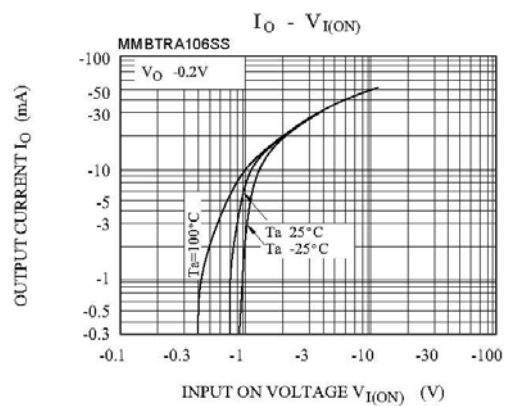
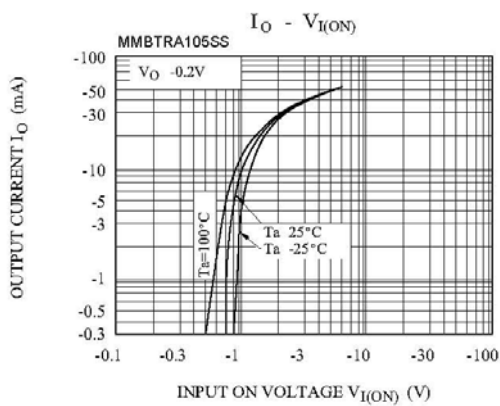
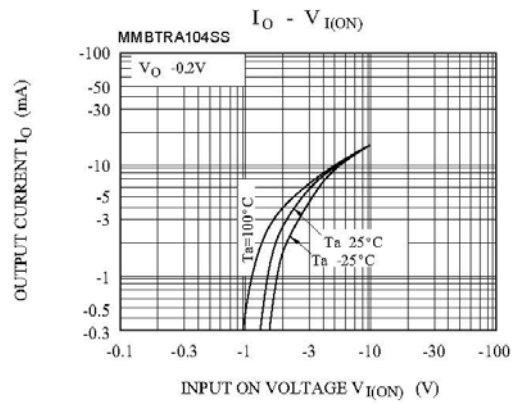
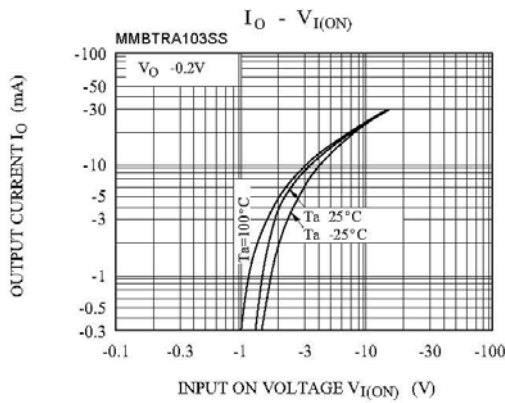
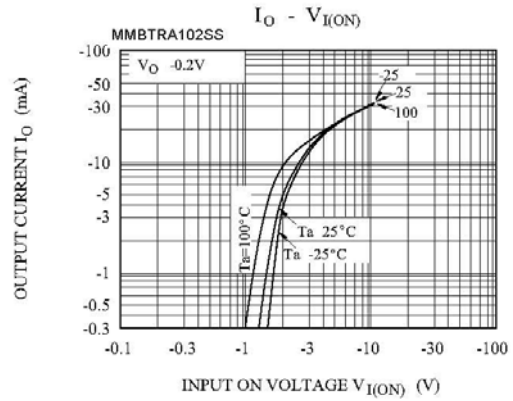
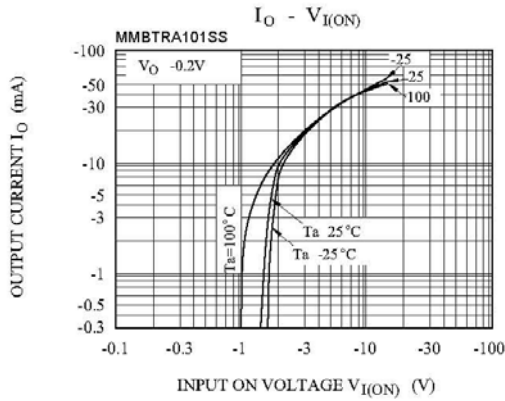


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Dated : 16/03/2015 Rev:01

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ISO/TS 16949:2009
Certificate No. 180713000



ISO14001:2004
Certificate No. 7116



ISO 9001:2008
Certificate No. 90719410

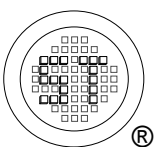
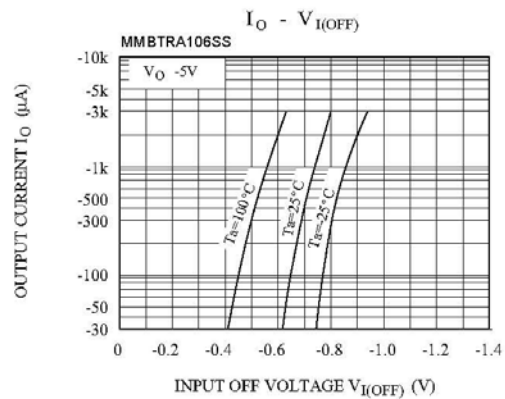
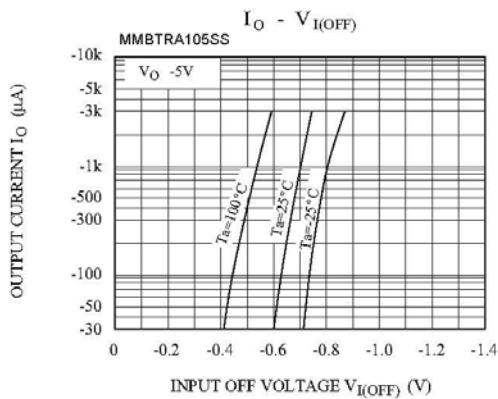
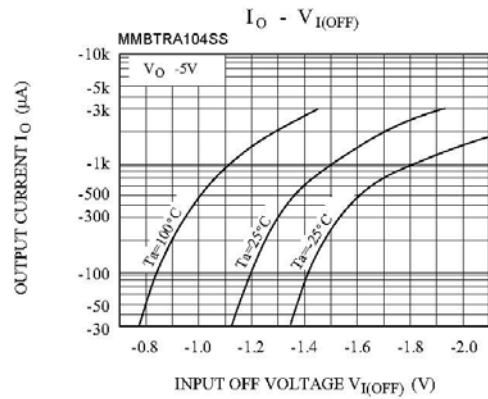
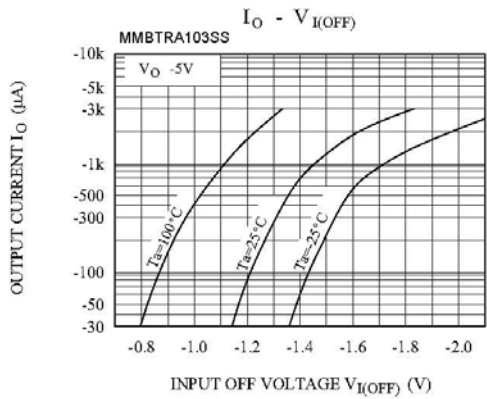
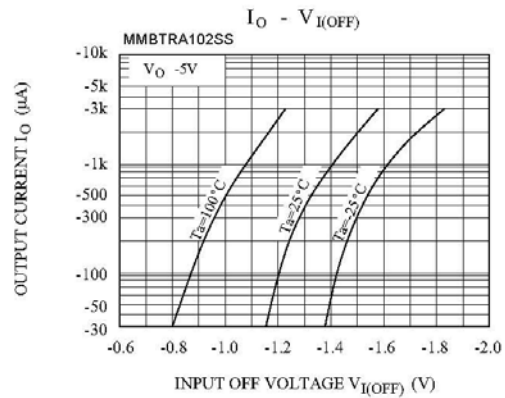
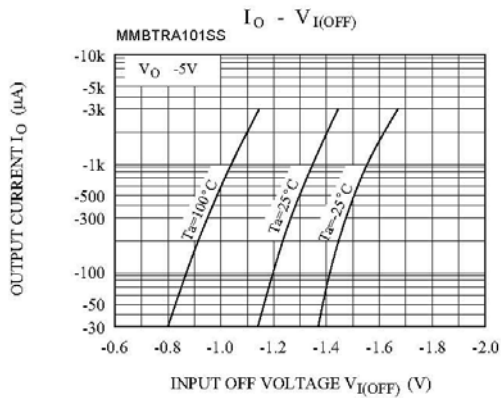


BS-OHSAS 18001:2007
Certificate No. 7116



IECQ QC 080000
Certificate No. FPC18P41483

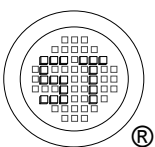
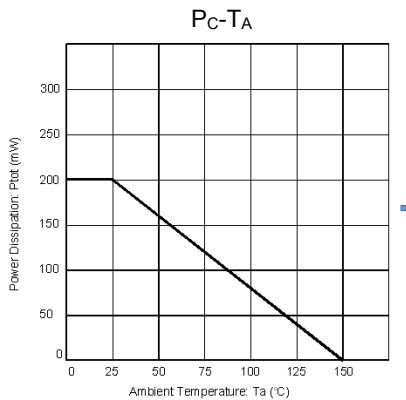
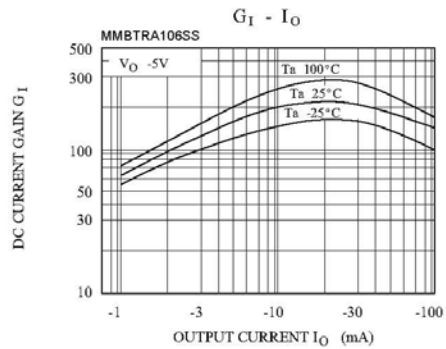
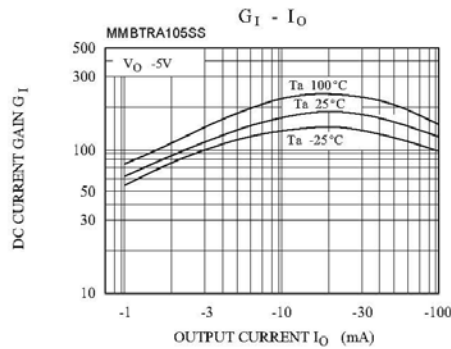
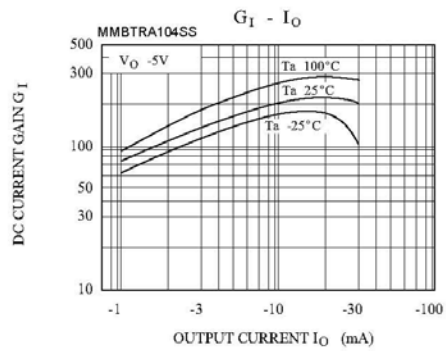
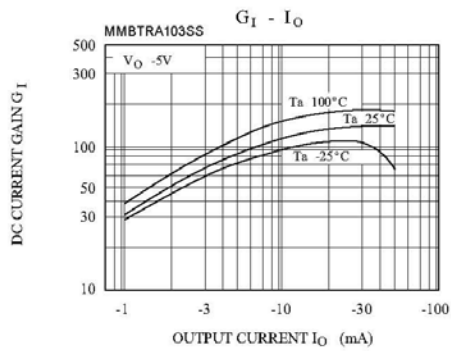
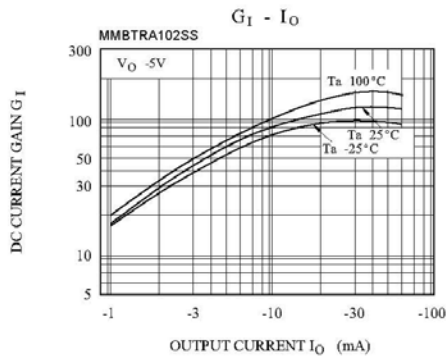
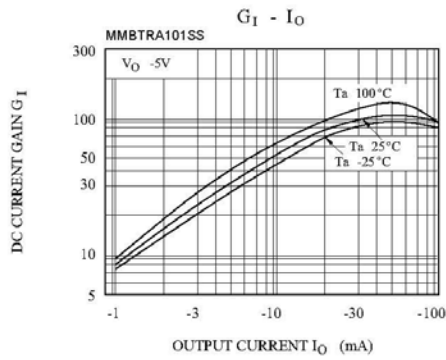
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